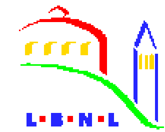
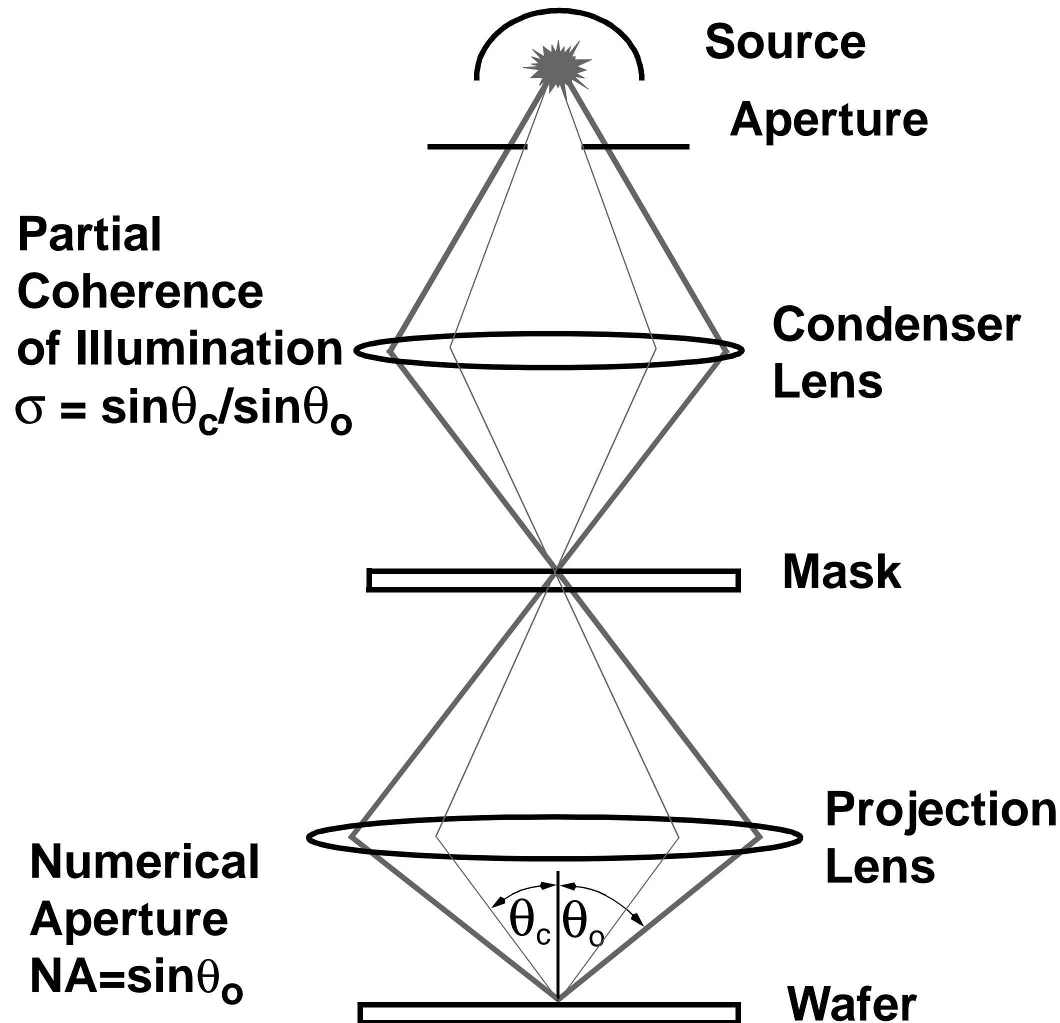
LITHOGRAPHY STEPPER OPTICS





Lithography Handbook

Minimum feature size (resolution)

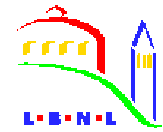
$MFS = k_1\lambda/NA$
$k_1 \approx 0.8$
(resist/enhancements)

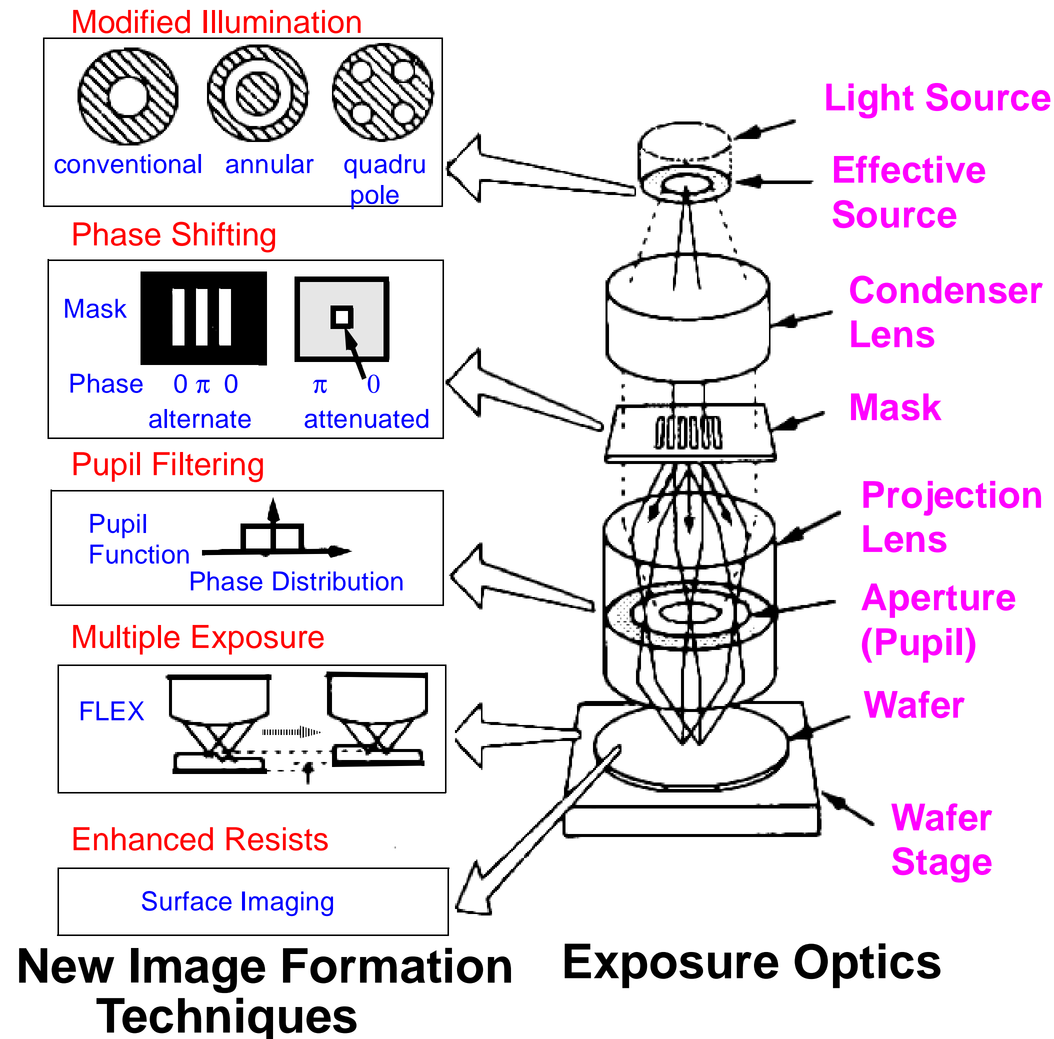
Depth of Focus

$DOF = k_2\lambda/(NA)^2$
$k_1 \approx 1$
(enhancements)

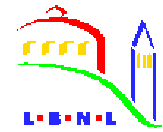
WHAT A DEEP-UV STEPPER REALLY LOOKS LIKE

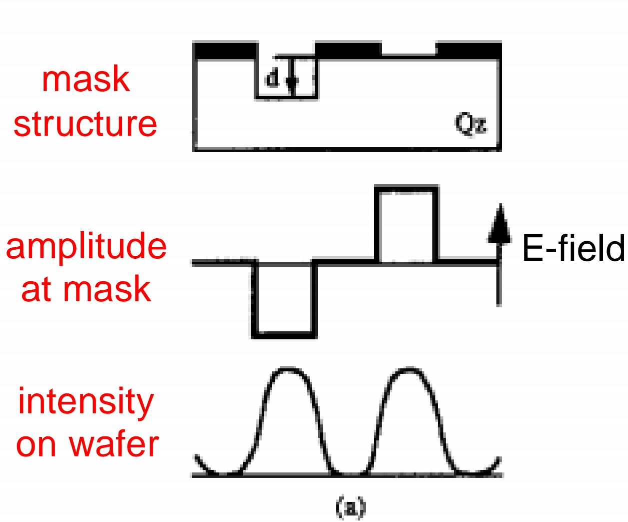
"WAVEFRONT ENGINEERING" TECHNIQUES IN PHOTOLITHOGRAPHY

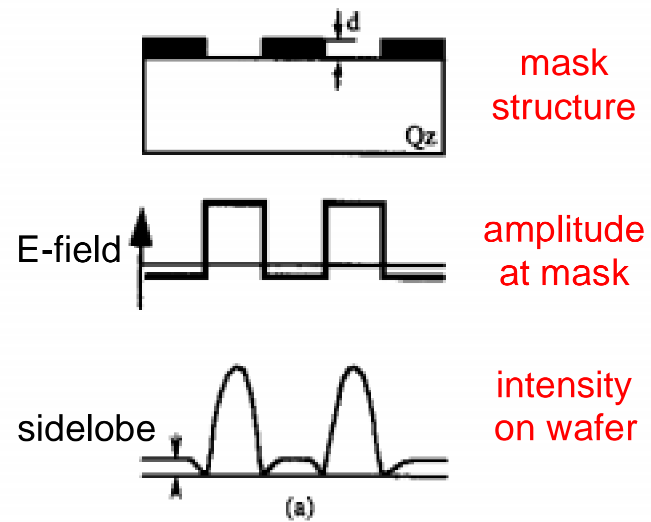




PHASE-SHIFT MASK TECHNIQUES



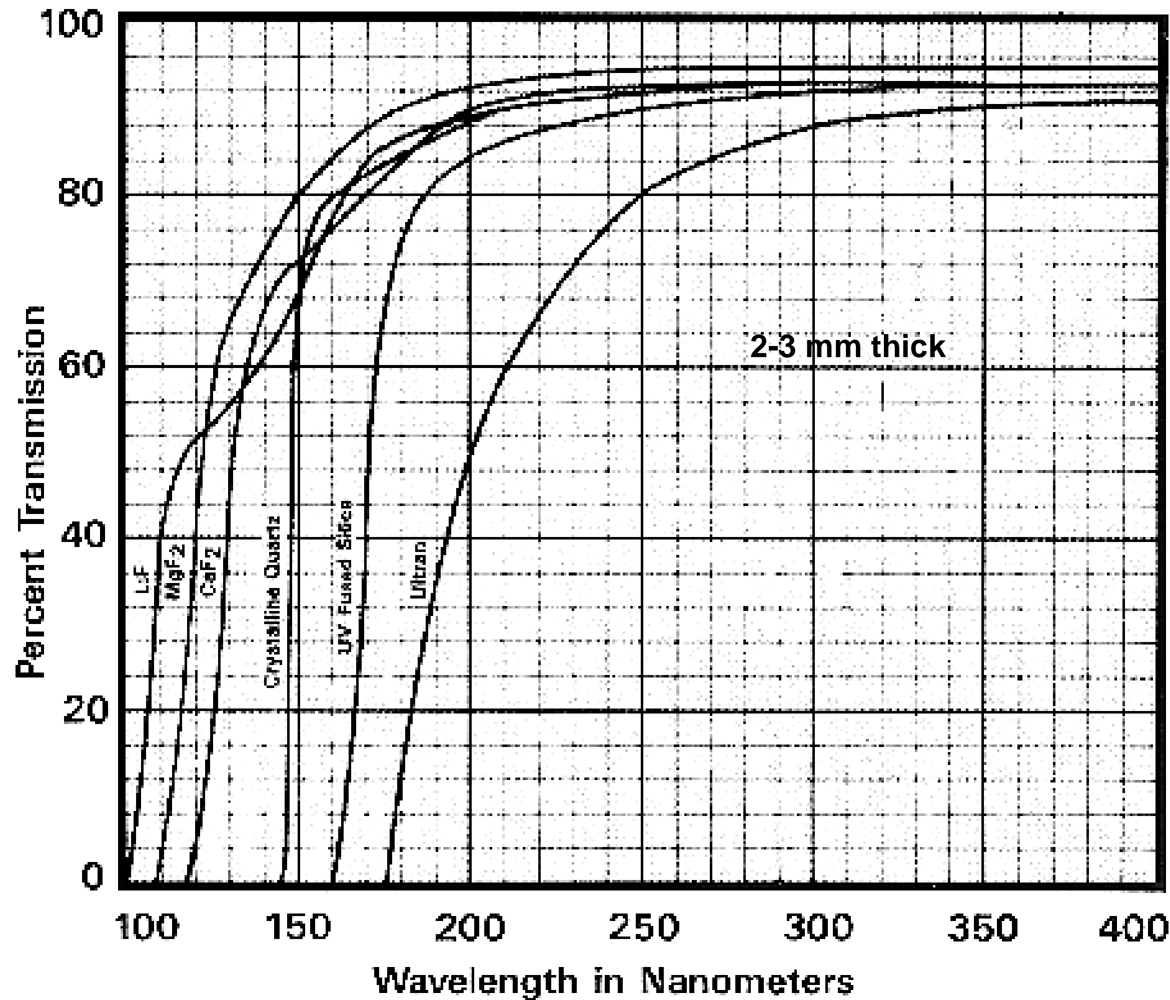




Alternating phase mask
(Levenson)

Attenuated phase mask

VACUUM ULTRAVIOLET TRANSMISSION CUTOFFS OF AVAILABLE OPTICAL MATERIALS



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CONTINUED EXTENSION OF OPTICAL PROJECTION

- Historical approach: (MFS = $k_1\lambda/NA$)

  $\Rightarrow$ Increase NA

  $\Rightarrow$ Decrease λ

  $\Rightarrow$ Decrease k_1

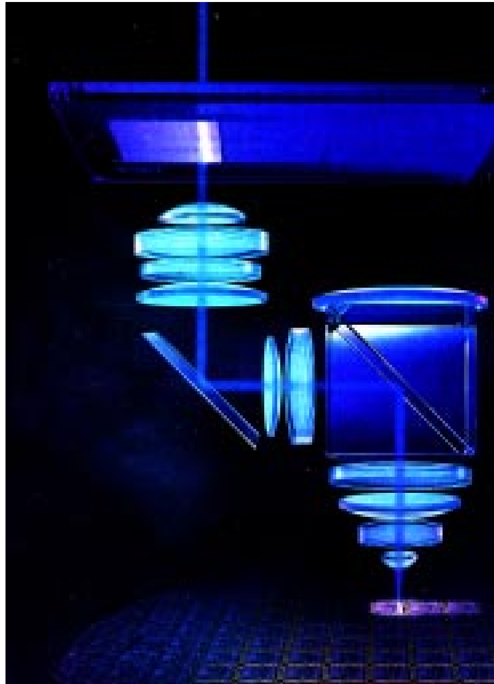
- Transmission optics reach to 193 nm

  - Expect limiting NA ≈ 0.75, $k_1 \approx 0.5$ $\Rightarrow$ MFS $\approx$ 130 nm

- What about Vacuum UV? (λ = 100 nm - 200 nm range)

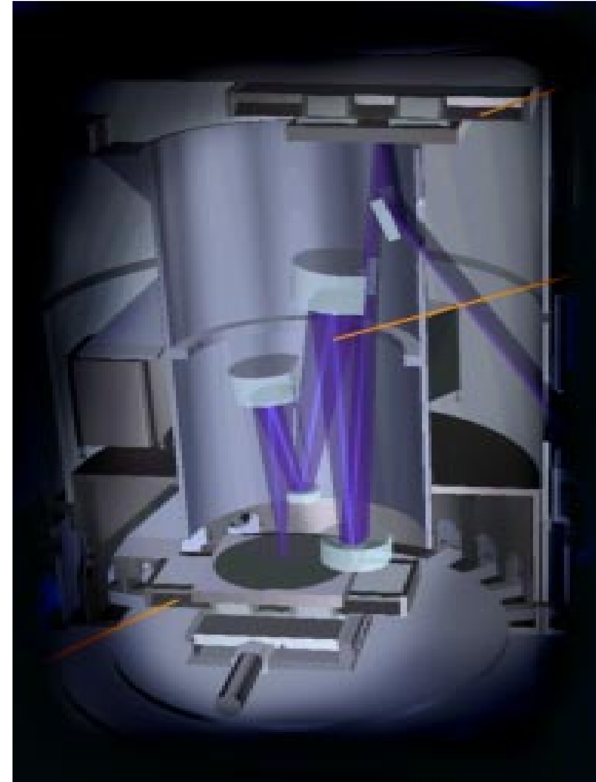
  - Diminishing returns absent further NA increase

OPTICAL LITHOGRAPHY TODAY (1997)
0.25 μm FEATURE SIZE



DUV (248 nm), Catadioptric optics

OPTICAL LITHOGRAPHY IN THE FUTURE
100 nm $\longrightarrow$ 30 nm FEATURE SIZE



EUV (13 nm), All-reflective optics, Reflection mask

EUVL ENGINEERING TEST STAND

Reticle Stage ISI Concept

Projection Optics

Collector

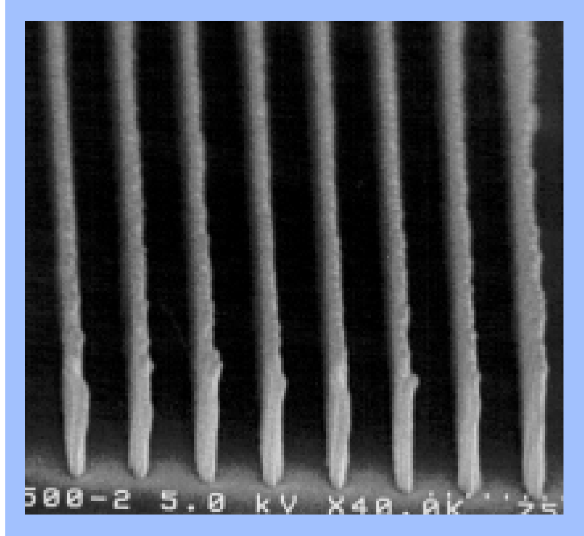
Laser Plasma Source

Wafer Stage ISI Concept

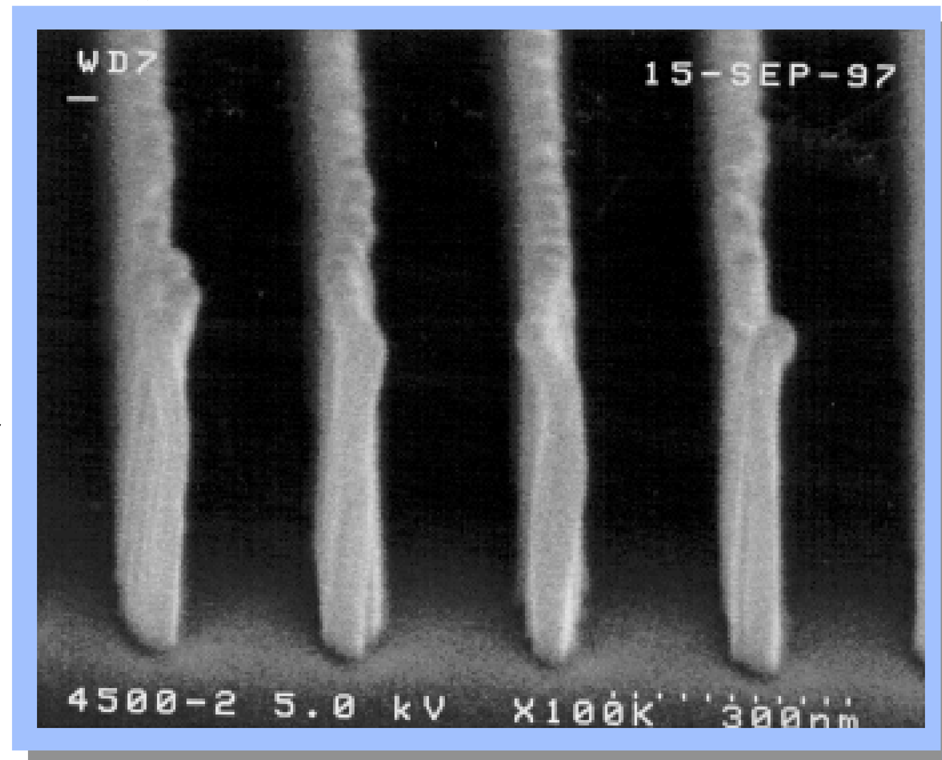
MAIN VACUUM CHAMBER

SOURCE VACUUM CHAMBER

1997 Resist / EUVL Imaging Status



TSI process
No crosslinker
Etch selectivity 45:1



70 nm lines

70 nm lines/spaces (2:1 pitch)
Coded for 70nm
15.6 mJ/cm² dose
10x microstepper

VNL Virtual National Laboratory

EUVL

EUVL Trend

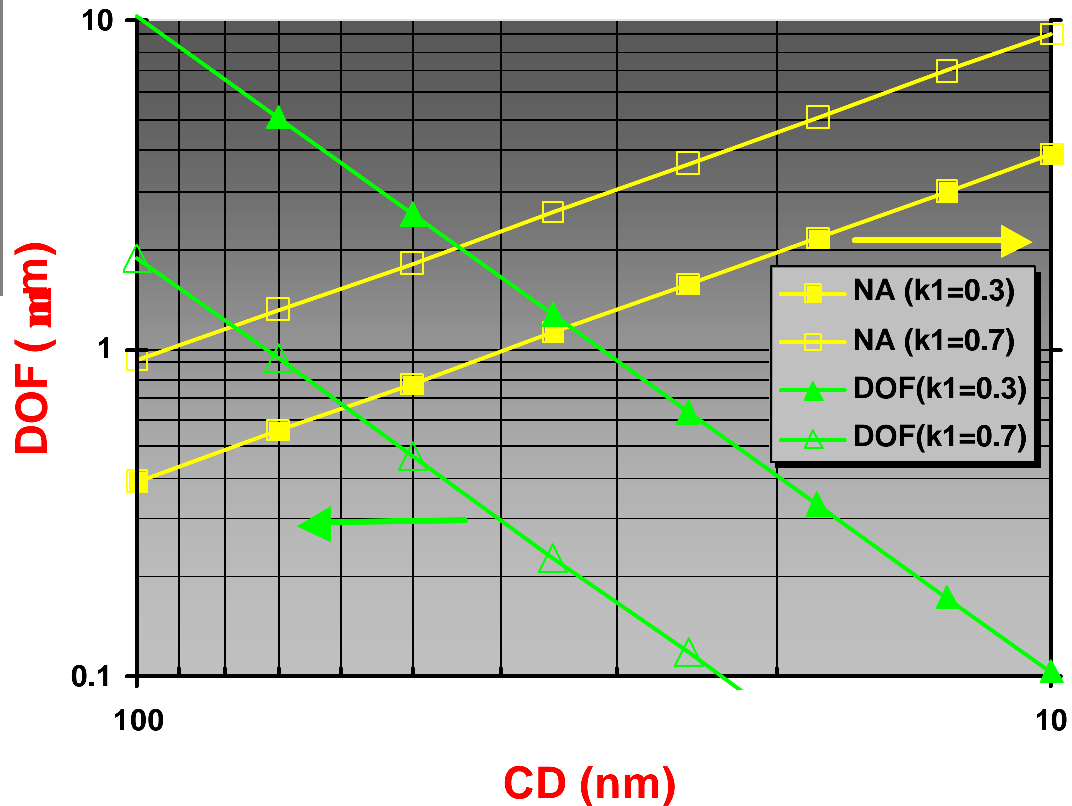
Lithography "Laws"

- CD = $k_1 * \lambda / NA$
- DOF = $1.2 * \lambda / NA^2$

"k_1 factor"

Conventional: $k_1 = 0.7$

Strong PSM: $k_1 = 0.3$



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